

## PMPB20XPE

# 20 V, single P-channel Trench MOSFET 30 November 2012

**Product data sheet** 

## **Product profile**

#### 1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 1.2 Features and benefits

- 2.4 kV ESD protected
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection

#### 1.3 Applications

- Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portable devices
- Hard disk and computing power management

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V	
$V_{GS}$	gate-source voltage			-12	-	12	V	
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}; t \le 5 \text{ s}$	[1]	-	-	-10.3	Α	
Static characte	Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; $I_D$ = -7.2 A; $T_j$ = 25 °C		-	19	23.5	mΩ	

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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## **Pinning information**

Table 2. **Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	D	drain	1 6	D I	
2	D	drain	7 7		
3	G	gate		G T	
4	S	source	3 8 4		
5	D	drain	Transparent top view DFN2020MD-6 (SOT1220)	<b>DFN2020MD-6 (SOT1220)</b>	
6	D	drain			S 017aaa259
7	D	drain			
8	S	source			

#### **Ordering information** 3.

Table 3. **Ordering information** 

Type number	Package					
	Name	Description	Version			
PMPB20XPE	DFN2020MD-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

#### **Marking** 4.

Table 4. **Marking codes** 

Type number	Marking code
PMPB20XPE	1D

#### **Limiting values 5**.

Table 5. **Limiting values** 

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
V <sub>GS</sub>	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-10.3	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-7.2	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-4.5	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10$ μs		-	-30	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[1]	-	1.7	W
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Symbol	Parameter	Conditions		Min	Max	Unit
		T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	3.5	W
		T <sub>sp</sub> = 25 °C		-	12.5	W
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain	diode		•			
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1.9	Α
ESD maximu	m rating			,		
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[2]	-	2400	V

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Measured between all pins.

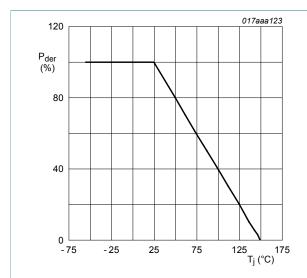


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

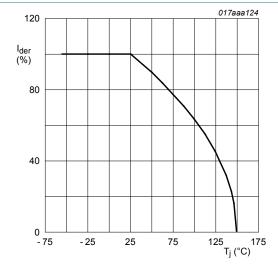


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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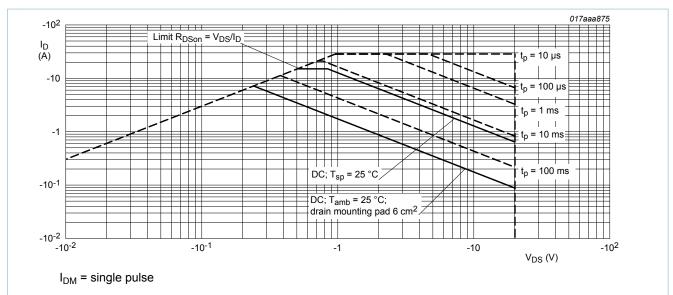


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient			[1]	-	235	270	K/W
	•		[2]	-	67	74	K/W
	anibient	in free air; t ≤ 5 s	[2]	-	33	36	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	5	10	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

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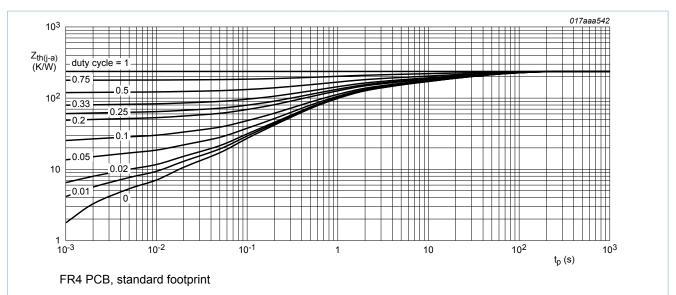


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

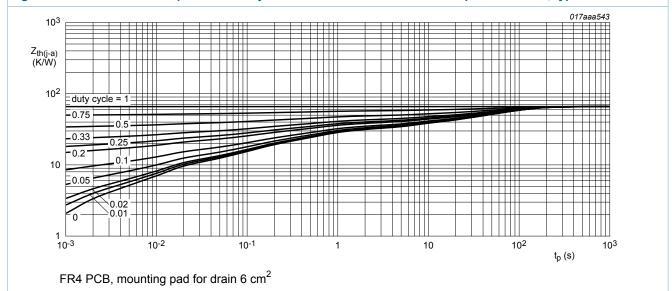


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

### 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	Static characteristics						
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$		-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 °C$		-0.47	-0.68	-0.9	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = -20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C		-	-	-1	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$		-	-	-10	μA
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Symbol	Parameter	Conditions	N	/lin	Тур	Max	Unit
		$V_{GS} = 8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-	10	μΑ
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -4.5 V; $I_{D}$ = -7.2 A; $T_{j}$ = 25 °C	-	-	19	23.5	mΩ
	resistance	$V_{GS}$ = -4.5 V; $I_{D}$ = -7.2 A; $T_{j}$ = 150 °C	-	-	27	33	mΩ
		$V_{GS}$ = -2.5 V; $I_{D}$ = -6.4 A; $T_{j}$ = 25 °C	-	-	22	29	mΩ
		$V_{GS}$ = -1.8 V; $I_D$ = -3.7 A; $T_j$ = 25 °C	-	-	28	39	mΩ
g <sub>fs</sub>	forward transconductance	$V_{DS}$ = -10 V; $I_{D}$ = -7.2 A; $T_{j}$ = 25 °C	-	-	50	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	-	5.2	-	Ω
Dynamic c	haracteristics						
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -10 V; $I_{D}$ = -7.2 A; $V_{GS}$ = -4.5 V;	-	-	30	45	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	-	4.1	-	nC
$Q_{GD}$	gate-drain charge		-	-	7.1	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = -10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	-	2945	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	-	245	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	-	210	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; $I_{D}$ = -7.2 A; $V_{GS}$ = -4.5 V;	-	-	13	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	-	60	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	-	92	-	ns
t <sub>f</sub>	fall time		-	-	50	-	ns
Source-dra	ain diode	1	<u> </u>		1	1	
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -1.9 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-0.7	-1.2	V
		I .					

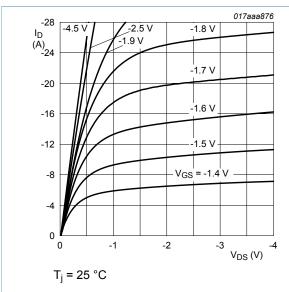


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

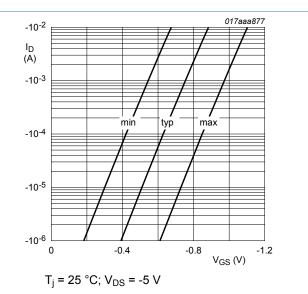


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

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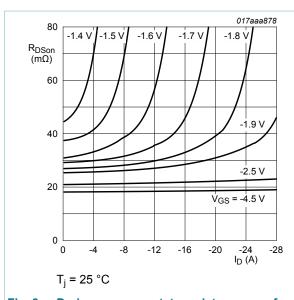


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

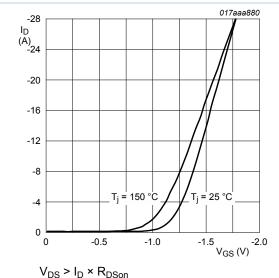


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

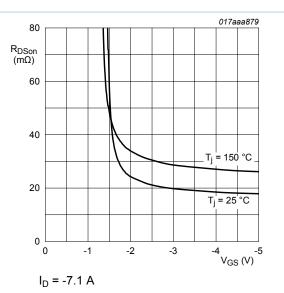


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

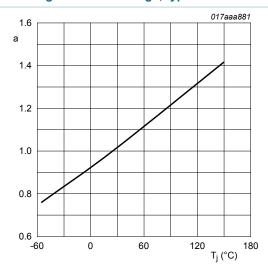


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

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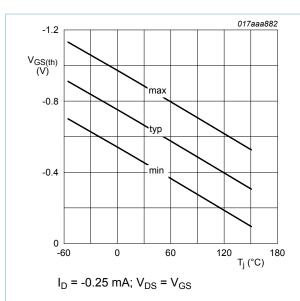


Fig. 12. Gate-source threshold voltage as a function of junction temperature

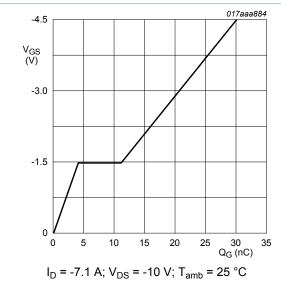


Fig. 14. Gate-source voltage as a function of gate charge; typical values

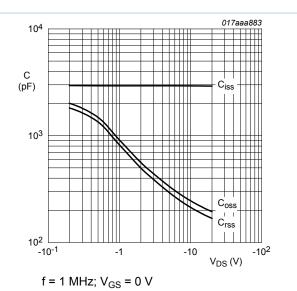


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

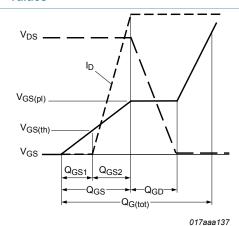
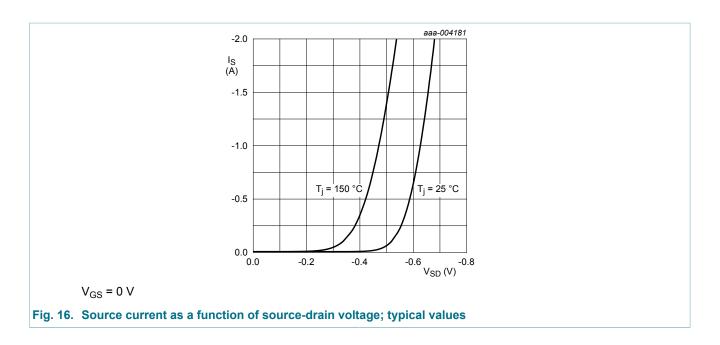


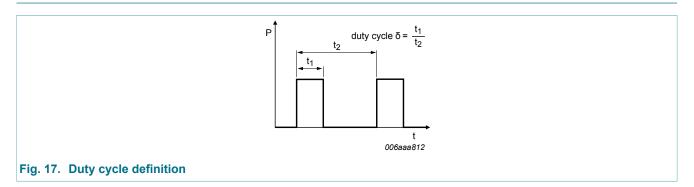
Fig. 15. MOSFET transistor: Gate charge waveform definitions

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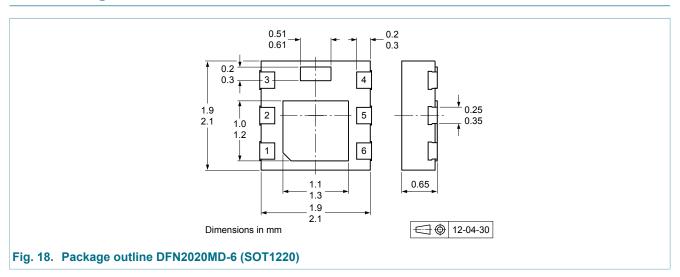
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## 8. Test information



## 9. Package outline

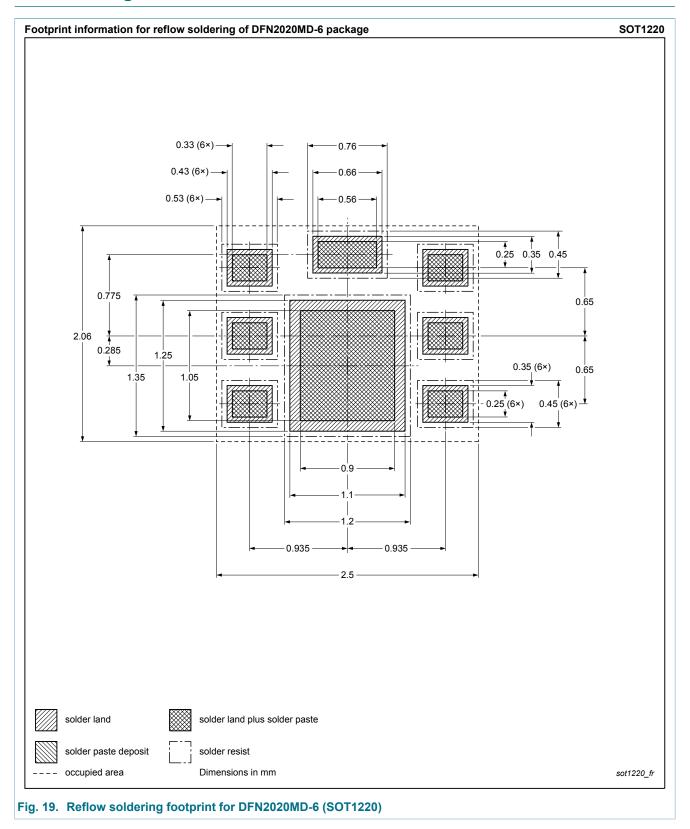


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## 10. Soldering



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## 11. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB20XPE v.1	20121130	Product data sheet	-	-

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## 12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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